

2SJ163

Silicon P-Channel Junction FET

For general switching

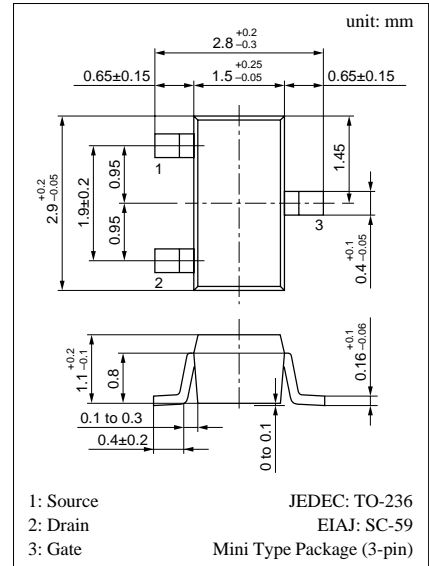
Complementary to 2SK1103

■ Features

- Low ON-resistance
- Low-noise characteristics

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Rated	Unit
Gate to Drain voltage	V_{GDS}	65	V
Drain current	I_D	-20	mA
Gate current	I_G	-10	mA
Allowable power dissipation	P_D	150	mW
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C



Marking Symbol (Example): 4M

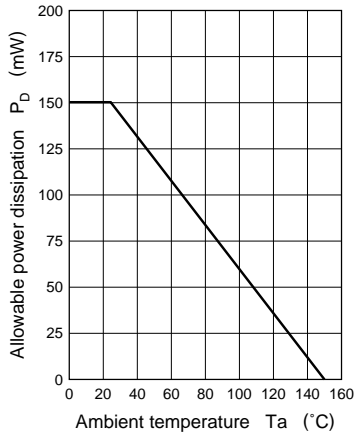
■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I_{DSS}^*	$V_{DS} = -10V, V_{GS} = 0$	-0.2		-6	mA
Gate to Source leakage current	I_{GSS}	$V_{GS} = 30V, V_{DS} = 0$			10	nA
Gate to Drain voltage	V_{GDS}	$I_G = 10\mu A, V_{DS} = 0$	65			V
Gate to Source cut-off voltage	V_{GSC}	$V_{DS} = -10V, I_D = -10\mu A$		1.5	3.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -1mA, f = 1kHz$	1.8	2.5		mS
Drain to Source ON-resistance	$R_{DS(on)}$	$V_{DS} = -10mV, V_{GS} = 0$		300		Ω
Input capacitance (Common Source)	C_{iss}	$V_{DS} = -10V, V_{GS} = 0, f = 1MHz$		12		pF
Reverse transfer capacitance (Common Source)	C_{rss}			4		pF

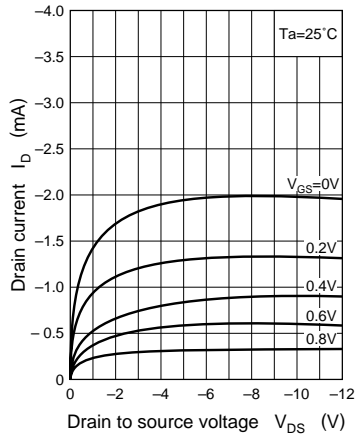
* I_{DSS} rank classification

Rank	O	P	Q	R
I_{DSS} (mA)	-0.2 to -1	-0.6 to -1.5	-1 to -3	-2.5 to -6
Marking Symbol	4MO	4MP	4MQ	4MR

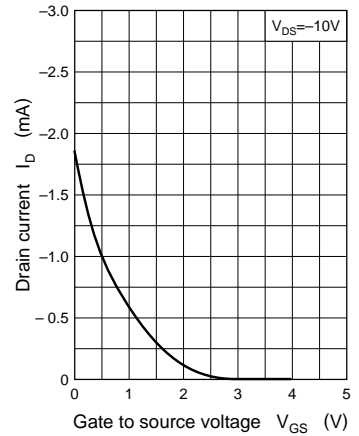
$P_D - T_a$



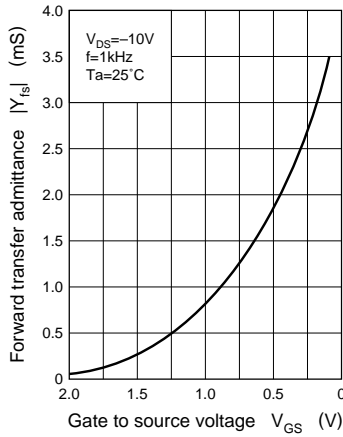
$I_D - V_{DS}$



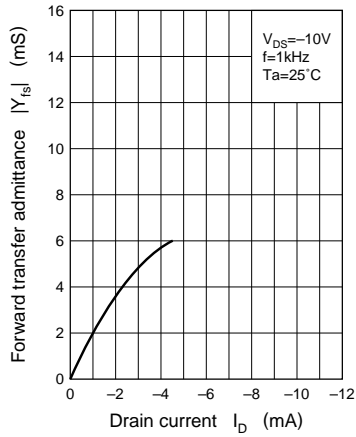
$I_D - V_{GS}$



$|Y_{fs}| - V_{GS}$



$|Y_{fs}| - I_D$



$C_{iss}, C_{oss}, C_{rss} - V_{DS}$

